

N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

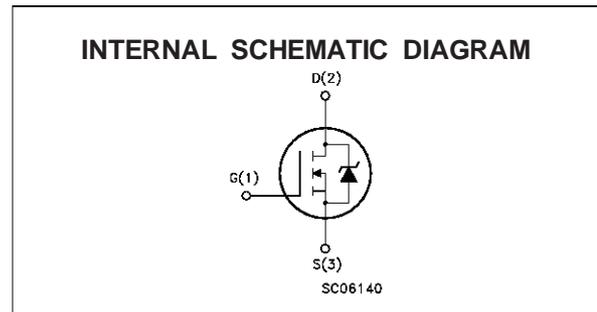
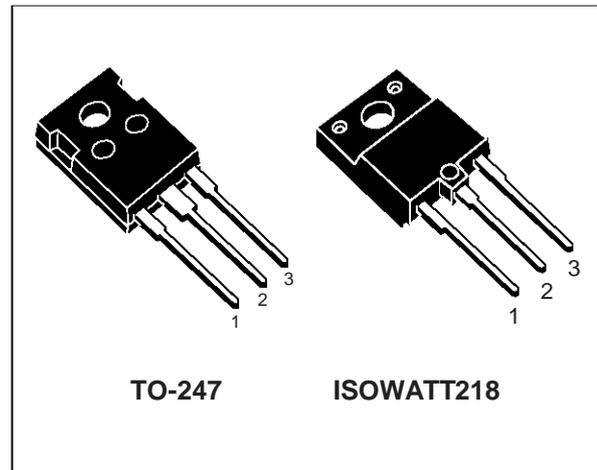
PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW5NA90	900 V	< 2.5 Ω	5.3 A
STH5NA90FI	900 V	< 2.5 Ω	3.5 A

- TYPICAL R_{DS(on)} = 2.1 Ω
- ± 30 V GATE-TO-SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- GATE CHARGE MINIMISED
- REDUCED THRESHOLD VOLTAGE SPREAD

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW5NA90	STH5NA90FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	900		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	900		V
V _{GS}	Gate-source Voltage	± 30		V
I _D	Drain Current (continuous) at T _c = 25 °C	5.3	3.5	A
I _D	Drain Current (continuous) at T _c = 100 °C	3.4	2.2	A
I _{DM} (●)	Drain Current (pulsed)	21.2	21.2	A
P _{tot}	Total Dissipation at T _c = 25 °C	150	60	W
	Derating Factor	1.2	0.48	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

STW5NA90-STH5NA90FI

THERMAL DATA

		TO-247	ISOWATT218		
R _{thj-case}	Thermal Resistance Junction-case	Max	0.83	2.08	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30		°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	5.3	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	520	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	900			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 100 °C			25 250	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 30 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2.25	3	3.75	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 2.5 A V _{GS} = 10V I _D = 2.5 A T _c = 100°C		2.1	2.5 5	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V	5.3			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 2.5 A	4	6.4		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		1350	1900	pF
C _{oss}	Output Capacitance			150	210	pF
C _{rss}	Reverse Transfer Capacitance			40	60	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 450\text{ V}$ $I_D = 2.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		13 12	20 19	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 720\text{ V}$ $R_G = 47\ \Omega$ $I_D = 5\text{ A}$ $V_{GS} = 10\text{ V}$		250		A/ μs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 720\text{ V}$ $I_D = 5\text{ A}$ $V_{GS} = 10\text{ V}$		60 10 26	80	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 720\text{ V}$ $R_G = 4.7\ \Omega$ $I_D = 5\text{ A}$ $V_{GS} = 10\text{ V}$		15 7 25	25 14 40	ns ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				5.3 21.3	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 5.3\text{ A}$ $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 5\text{ A}$ $V_{DD} = 30\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ $T_j = 150\text{ }^\circ\text{C}$		1150 17.3 30		ns μC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area